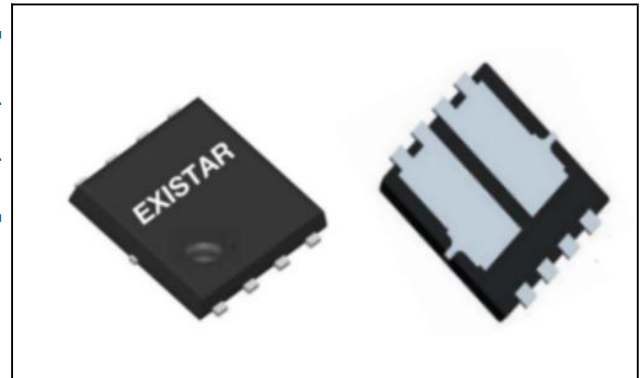


## N-Channel 30V MOSFET

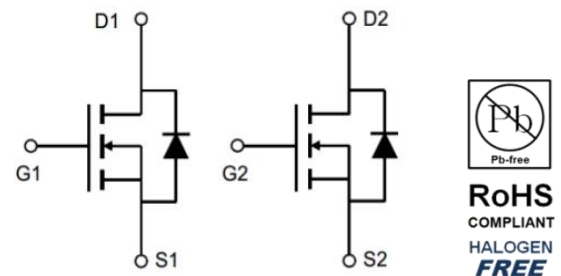
### E030N8P0KL1

|    | V <sub>DS</sub> (V) | R <sub>DS(on),max</sub> (mΩ) | I <sub>D</sub> (A) |
|----|---------------------|------------------------------|--------------------|
| N1 | 30V                 | 8.0 @ V <sub>GS</sub> = 10V  | 45                 |
| N2 | 30V                 | 8.0 @ V <sub>GS</sub> = 10V  | 45                 |

**PDFN5\*6D**


### Features

- Low R<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested



### Applications

- DC/DC conversion
- Power switch
- Moto driver

### Package And Ordering Information

| Ordering code | Package  | Marking     |
|---------------|----------|-------------|
| E030N8P0KL1   | PDFN5*6D | E030N8P0KL1 |

### Ordering Information

| Package  | Units/ Reel | Reels/ Inner Box | Units/ Inner Box |
|----------|-------------|------------------|------------------|
| PDFN5*6D | 5000        | 1                | 5000             |

**Key Performance Parameters**

| Parameter              | Value | Unit |
|------------------------|-------|------|
| VDS, min @ Tj(max)     | 30    | V    |
| ID, pulse              | 146   | A    |
| RDS(ON), max @ VGS=10V | 8.0   | mΩ   |
| Qg                     | 21.6  | nC   |

**Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted**

| Parameter  | Symbol                            | Limit                 | Unit |
|--|-----------------------------------|-----------------------|------|
| Drain-source voltage                             | V <sub>DS</sub>                   | 30                    | V    |
| Gate-source voltage                              | V <sub>GS</sub>                   | ±20                   |      |
| Continuous drain current                         | I <sub>D</sub>                    | T <sub>A</sub> =25°C  | 45   |
|  |                                   | T <sub>A</sub> =100°C | 32   |
| Pulsed drain current                             | I <sub>D,pulse</sub>              | 146                   | A    |
| Avalanche energy, single pulse                   | E <sub>AS</sub>                   | 38                    | mJ   |
| Power dissipation                                | P <sub>D</sub>                    | T <sub>A</sub> =25°C  | 42   |
|  |                                   | T <sub>A</sub> =100°C | 3.2  |
| Operating junction and storage temperature range | T <sub>J</sub> , T <sub>stg</sub> | -55 To 175            | °C   |

**Thermal Characteristics**

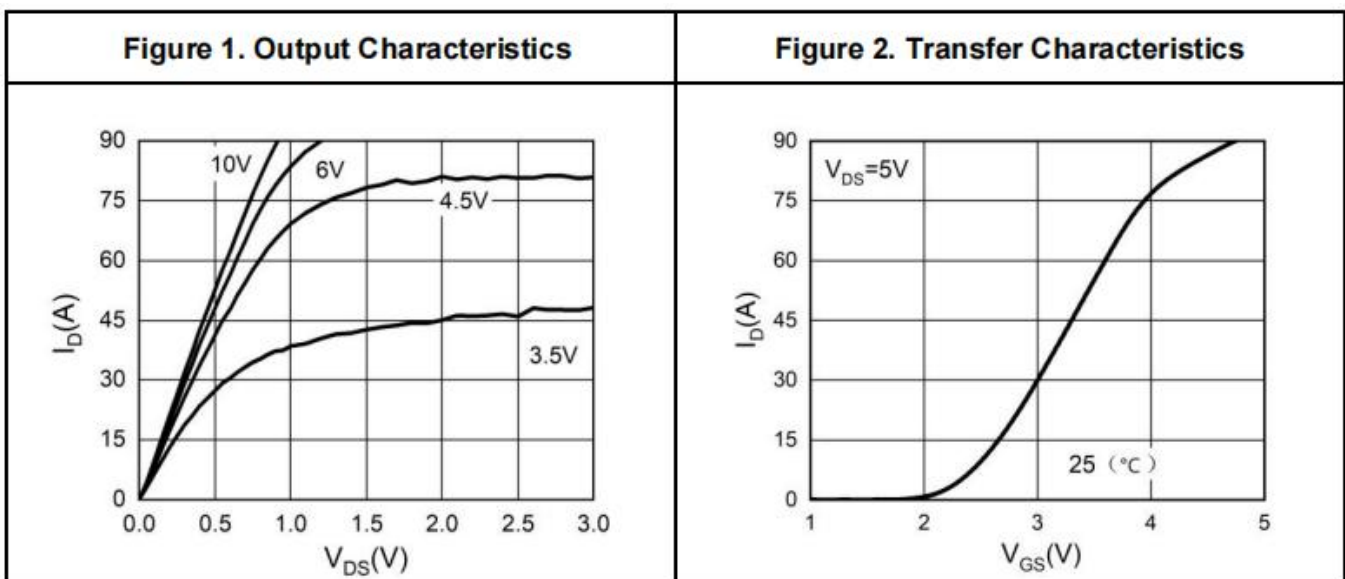
| Parameter                               | Symbol           | Max. | Unit |
|---|------------------|------|------|
| Thermal resistance, junction-to-case    | R <sub>θJC</sub> | 2.6  | °C/W |
| Thermal resistance, junction-to-ambient | R <sub>θJA</sub> | 60   |      |

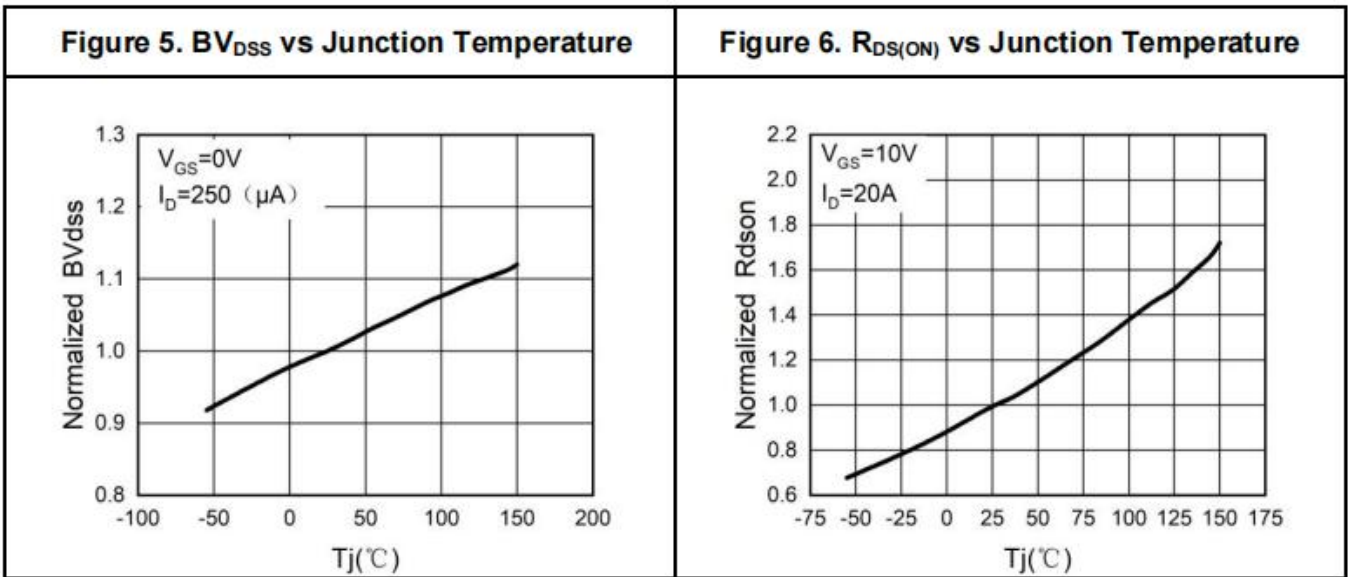
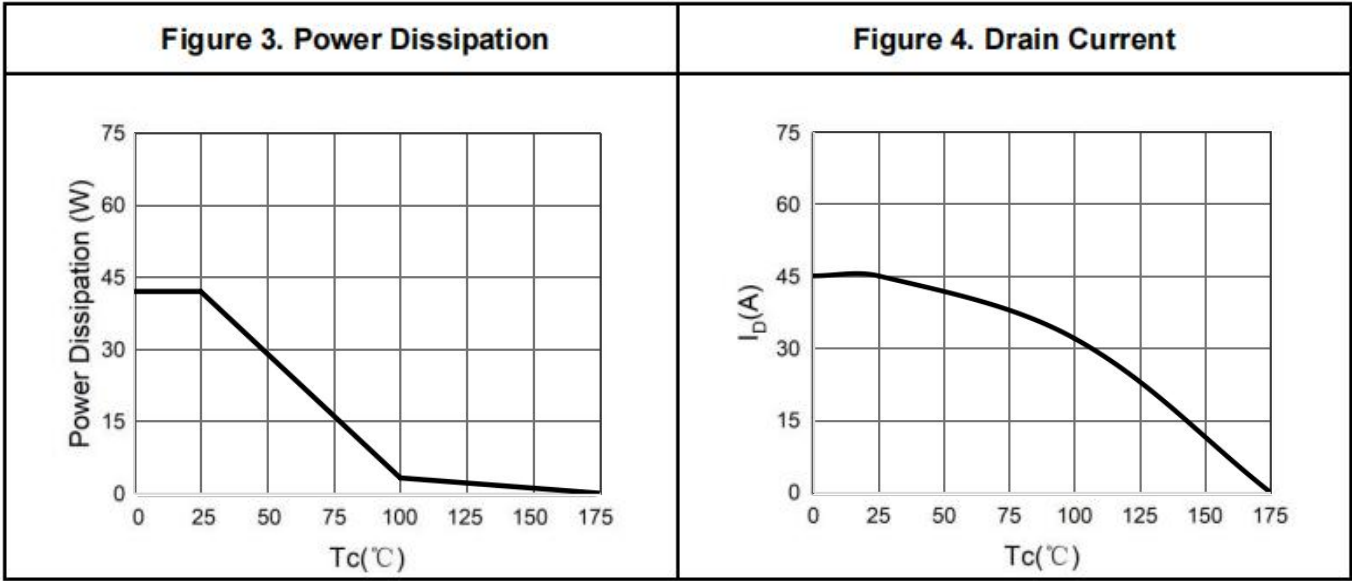
**Electrical Characteristics at Tj=25°C unless otherwise specified**

| Parameter                         | Symbol               | Min. | Typ. | Max. | Unit | Test conditions   |
|-----------------------------------|----------------------|------|------|------|------|---|
| <b>Static</b>                     |                      |      |      |      |      |   |
| Drain to source breakdown voltage | V <sub>(BR)DSS</sub> | 30   |      |      | V    | V <sub>GS</sub> = 0, I <sub>D</sub> = 250 μA                |
| Gate-source threshold voltage     | V <sub>GS(th)</sub>  | 1    |      | 2.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA |
| Gate-body leakage                 | I <sub>GSS</sub>     |      |      | ±100 | nA   | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V              |
| Zero gate voltage drain current   | I <sub>DSS</sub>     |      |      | 1    | μA   | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V               |
| Drain-source on-resistance        | R <sub>DS(on)</sub>  |      | 6.8  | 8    | mΩ   | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A               |
| Drain-source on-resistance        | R <sub>DS(on)</sub>  |      | 9.8  | 12   | mΩ   | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A              |
| Forward transconductance          | g <sub>fs</sub>      |      | 18   |      | S    | V <sub>DS</sub> = 5 V, I <sub>D</sub> = 20 A                |

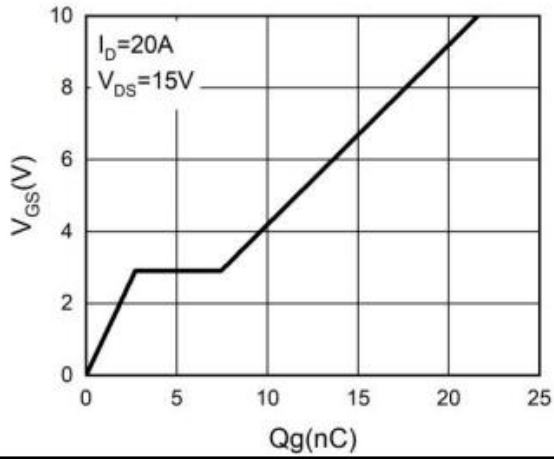
|                              |                     |  |      |     |    |  |
|------------------------------|---------------------|--|------|-----|----|--|
| Gate resistance              | R <sub>g</sub>      |  | 1.8  |     | Ω  | f=1MHz   |
| <b>Gate Charge</b>           |                     |  |      |     |    |  |
| Total gate charge            | Q <sub>g</sub>      |  | 21.6 |     | nC | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A, V <sub>GS</sub> = 10 V                              |
| Gate-source charge           | Q <sub>gs</sub>     |  | 2.7  |     |    |  |
| Gate-drain charge            | Q <sub>gd</sub>     |  | 4.7  |     |    |  |
| <b>Dynamic</b>               |                     |  |      |     |    |  |
| Turn-on delay time           | t <sub>d(on)</sub>  |  | 12   |     | ns | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V,<br>R <sub>L</sub> = 0.75 Ω, R <sub>GEN</sub> = 3 Ω |
| Rise time                    | t <sub>r</sub>      |  | 2.4  |     |    |  |
| Turn-off delay time          | t <sub>d(off)</sub> |  | 30.4 |     |    |  |
| Fall time                    | t <sub>f</sub>      |  | 4    |     |    |  |
| Input capacitance            | C <sub>iss</sub>    |  | 1082 |     | pF | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1.0MHz  |
| Output capacitance           | C <sub>oss</sub>    |  | 147  |     |    |  |
| Reverse transfer capacitance | C <sub>rss</sub>    |  | 121  |     |    |  |
| <b>Body Diode</b>            |                     |  |      |     |    |  |
| Diode forward voltage        | V <sub>SD</sub>     |  |      | 1.2 | V  | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A   |
| Reverse recovery time        | t <sub>rr</sub>     |  | 19.4 |     | ns | I <sub>F</sub> = 20 A, di/dt = 500 A/μs  |
| Reverse recovery charge      | Q <sub>rr</sub>     |  | 11.6 |     | nC |  |

### Electrical Characteristics Diagrams

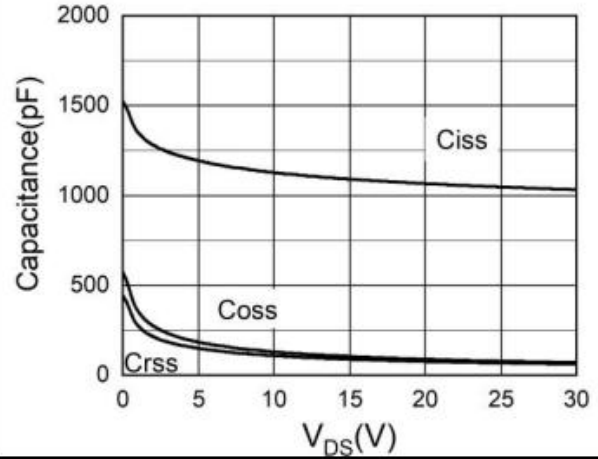




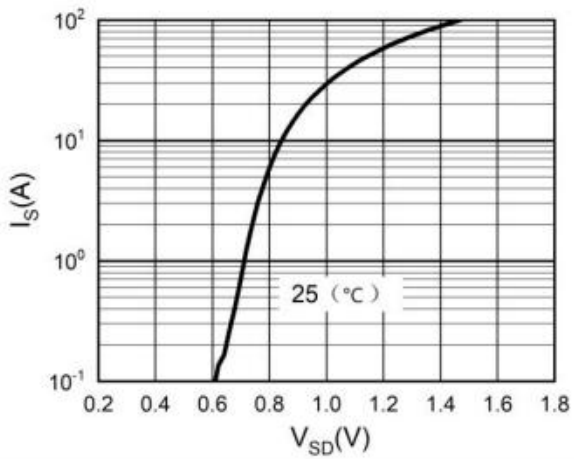
**Figure 7. Gate Charge Waveforms**



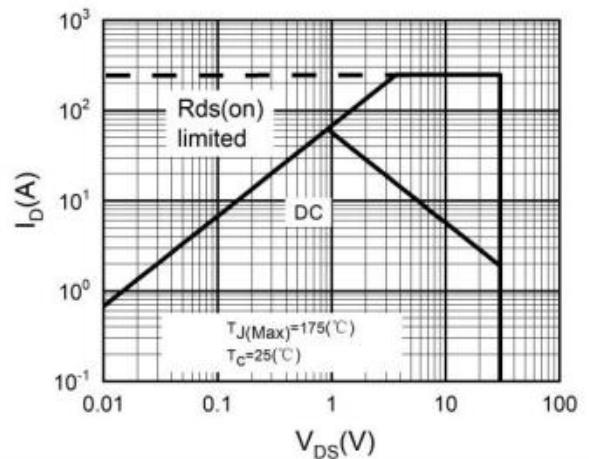
**Figure 8. Capacitance**

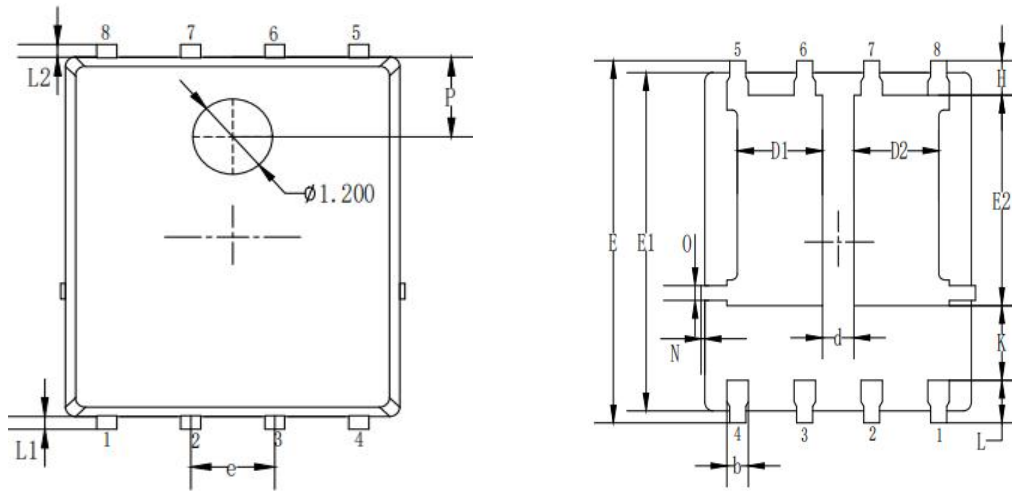


**Figure 9. Body-Diode Characteristics**



**Figure 10. Maximum Safe Operating Area**



**Package Outline Dimensions**


| Symbols  | Millimeters |      |      |
|----------|-------------|------|------|
|          | MIN.        | NOM. | MAX. |
| A        | 0.90        | 1.05 | 1.20 |
| b        | 0.35        | 0.40 | 0.50 |
| C        | 0.20        | 0.25 | 0.35 |
| D        | 4.90        | 5.05 | 5.20 |
| D1/D2    | 1.51        | 1.61 | 1.71 |
| d        | 0.50        | 0.60 | 0.70 |
| E        | 6.00        | 6.15 | 6.30 |
| E1       | 5.60        | 5.75 | 5.90 |
| E2       | 3.47        | 3.57 | 3.67 |
| e        | 1.27 BSC.   |      |      |
| H        | 0.48        | 0.58 | 0.68 |
| K        | 1.17        | 1.27 | 1.37 |
| L        | 0.64        | 0.74 | 0.84 |
| L1/L2    | 0.20 REF.   |      |      |
| $\theta$ | 8°          | 10°  | 12°  |
| M        | 0.08 REF.   |      |      |
| N        | 0           | -    | 0.15 |
| O        | 0.25 REF.   |      |      |
| P        | 1.28 REF.   |      |      |

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